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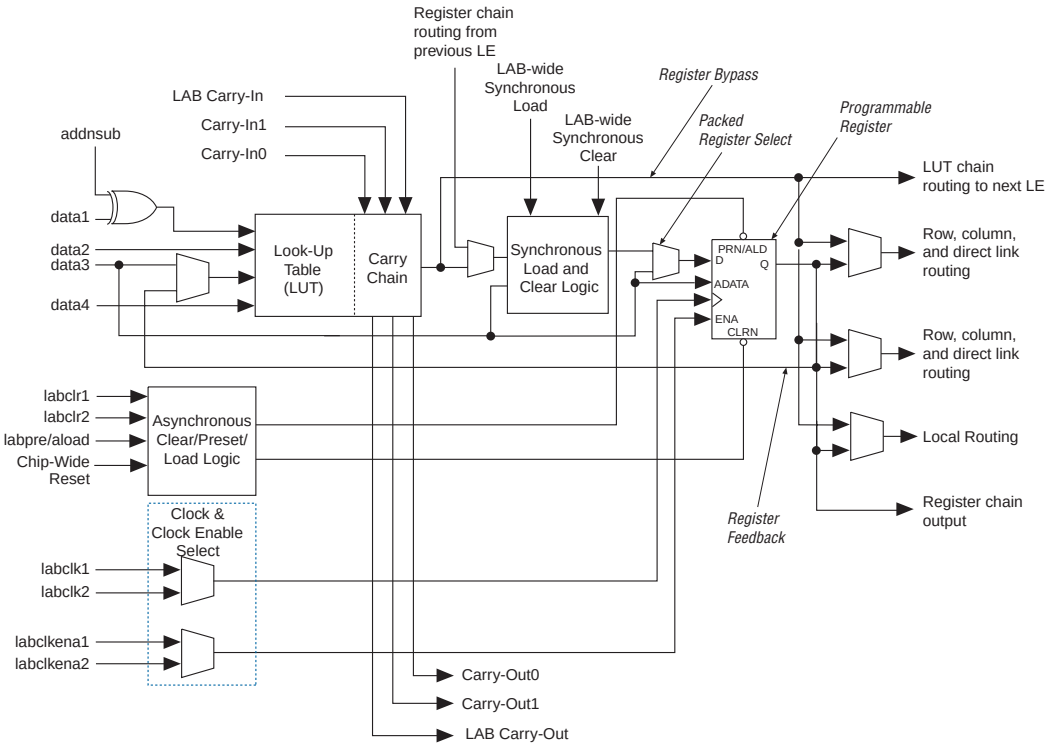
Details	
Product Status	Obsolete
Number of LABs/CLBs	7904
Number of Logic Elements/Cells	79040
Total RAM Bits	7427520
Number of I/O	1203
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1508-BBGA, FCBGA
Supplier Device Package	1508-FBGA, FC (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s80f1508c6aa

Contents

Chapter 3. Configuration & Testing

Chapter 4. DC & Switching Characteristics

Figure 2–5. Stratix LE



Each LE's programmable register can be configured for D, T, JK, or SR operation. Each register has data, true asynchronous load data, clock, clock enable, clear, and asynchronous load/preset inputs. Global signals, general-purpose I/O pins, or any internal logic can drive the register's clock and clear control signals. Either general-purpose I/O pins or internal logic can drive the clock enable, preset, asynchronous load, and asynchronous data. The asynchronous load data input comes from the `data3` input of the LE. For combinatorial functions, the register is bypassed and the output of the LUT drives directly to the outputs of the LE.

Each LE has three outputs that drive the local, row, and column routing resources. The LUT or register output can drive these three outputs independently. Two LE outputs drive column or row and direct link routing connections and one drives local interconnect resources. This allows the LUT to drive one output while the register drives another output. This feature, called register packing, improves device utilization because the device can use the register and the LUT for unrelated

Table 2–3. TriMatrix Memory Features (Part 2 of 2)

Memory Feature	M512 RAM Block (32 × 18 Bits)	M4K RAM Block (128 × 36 Bits)	M-RAM Block (4K × 144 Bits)
Configurations	512 × 1 256 × 2 128 × 4 64 × 8 64 × 9 32 × 16 32 × 18	4K × 1 2K × 2 1K × 4 512 × 8 512 × 9 256 × 16 256 × 18 128 × 32 128 × 36	64K × 8 64K × 9 32K × 16 32K × 18 16K × 32 16K × 36 8K × 64 8K × 72 4K × 128 4K × 144

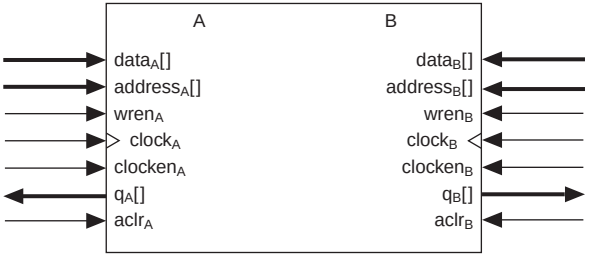
Notes to Table 2–3:
(1) See Table 4–36 for maximum performance information.
(2) The M-RAM block does not support memory initializations. However, the M-RAM block can emulate a ROM function using a dual-port RAM bock. The Stratix device must write to the dual-port memory once and then disable the write-enable ports afterwards.

Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Memory Modes

TriMatrix memory blocks include input registers that synchronize writes and output registers to pipeline designs and improve system performance. M4K and M-RAM memory blocks offer a true dual-port mode to support any combination of two-port operations: two reads, two writes, or one read and one write at two different clock frequencies. Figure 2–12 shows true dual-port memory.

Figure 2–12. True Dual-Port Memory Configuration



TriMatrix memory architecture can implement pipelined RAM by registering both the input and output signals to the RAM block. All TriMatrix memory block inputs are registered providing synchronous write cycles. In synchronous operation, the memory block generates its own self-timed strobe write enable (WREN) signal derived from the global or regional clock. In contrast, a circuit using asynchronous RAM must generate the RAM WREN signal while ensuring its data and address signals meet setup and hold time specifications relative to the WREN signal. The output registers can be bypassed. Flow-through reading is possible in the simple dual-port mode of M512 and M4K RAM blocks by clocking the read enable and read address registers on the negative clock edge and bypassing the output registers.

Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The Quartus II software automatically implements larger memory by combining multiple TriMatrix memory blocks. For example, two 256 × 16-bit RAM blocks can be combined to form a 256 × 32-bit RAM block. Memory performance does not degrade for memory blocks using the maximum number of words available in one memory block. Logical memory blocks using less than the maximum number of words use physical blocks in parallel, eliminating any external control logic that would increase delays. To create a larger high-speed memory block, the Quartus II software automatically combines memory blocks with LE control logic.

Clear Signals

When applied to input registers, the asynchronous clear signal for the TriMatrix embedded memory immediately clears the input registers. However, the output of the memory block does not show the effects until the next clock edge. When applied to output registers, the asynchronous clear signal clears the output registers and the effects are seen immediately.

Parity Bit Support

The memory blocks support a parity bit for each byte. The parity bit, along with internal LE logic, can implement parity checking for error detection to ensure data integrity. You can also use parity-size data words to store user-specified control bits. In the M4K and M-RAM blocks, byte enables are also available for data input masking during write operations.

The memory address depths and output widths can be configured as 4,096 × 1, 2,048 × 2, 1,024 × 4, 512 × 8 (or 512 × 9 bits), 256 × 16 (or 256 × 18 bits), and 128 × 32 (or 128 × 36 bits). The 128 × 32- or 36-bit configuration is not available in the true dual-port mode. Mixed-width configurations are also possible, allowing different read and write widths. Tables 2–5 and 2–6 summarize the possible M4K RAM block configurations.

Table 2–5. M4K RAM Block Configurations (Simple Dual-Port)

Read Port	Write Port								
	4K × 1	2K × 2	1K × 4	512 × 8	256 × 16	128 × 32	512 × 9	256 × 18	128 × 36
4K × 1	✓	✓	✓	✓	✓	✓			
2K × 2	✓	✓	✓	✓	✓	✓			
1K × 4	✓	✓	✓	✓	✓	✓			
512 × 8	✓	✓	✓	✓	✓	✓			
256 × 16	✓	✓	✓	✓	✓	✓			
128 × 32	✓	✓	✓	✓	✓	✓			
512 × 9							✓	✓	✓
256 × 18							✓	✓	✓
128 × 36							✓	✓	✓

Table 2–6. M4K RAM Block Configurations (True Dual-Port)

Port A	Port B						
	4K × 1	2K × 2	1K × 4	512 × 8	256 × 16	512 × 9	256 × 18
4K × 1	✓	✓	✓	✓	✓		
2K × 2	✓	✓	✓	✓	✓		
1K × 4	✓	✓	✓	✓	✓		
512 × 8	✓	✓	✓	✓	✓		
256 × 16	✓	✓	✓	✓	✓		
512 × 9						✓	✓
256 × 18						✓	✓

When the M4K RAM block is configured as a shift register block, you can create a shift register up to 4,608 bits ($w \times m \times n$).

Table 2–11. M-RAM Combined Byte Selection for ×144 Mode Notes (1), (2)	
byteena[15..0]	**datain ×144**
[0] = 1	[8..0]
[1] = 1	[17..9]
[2] = 1	[26..18]
[3] = 1	[35..27]
[4] = 1	[44..36]
[5] = 1	[53..45]
[6] = 1	[62..54]
[7] = 1	[71..63]
[8] = 1	[80..72]
[9] = 1	[89..81]
[10] = 1	[98..90]
[11] = 1	[107..99]
[12] = 1	[116..108]
[13] = 1	[125..117]
[14] = 1	[134..126]
[15] = 1	[143..135]

Notes to Tables 2–10 and 2–11:

(1) Any combination of byte enables is possible.

(2) Byte enables can be used in the same manner with 8-bit words, i.e., in ×16, ×32, ×64, and ×128 modes.

Similar to all RAM blocks, M-RAM blocks can have different clocks on their inputs and outputs. All input registers—`renwe`, `datain`, address, and byte enable registers—are clocked together from either of the two clocks feeding the block. The output register can be bypassed. The eight `labclk` signals or local interconnect can drive the control signals for the A and B ports of the M-RAM block. LEs can also control the `clock_a`, `clock_b`, `renwe_a`, `renwe_b`, `clr_a`, clr_b, `clocken_a`, and `clocken_b` signals as shown in Figure 2–19.

Adder/Subtractor/Accumulator

The adder/subtractor/accumulator is the first level of the adder/output block and can be used as an accumulator or as an adder/subtractor.

Adder/Subtractor
Each adder/subtractor/accumulator block can perform addition or subtraction using the `addnsub` independent control signal for each first-level adder in 18 × 18-bit mode. There are two `addnsub[1..0]` signals available in a DSP block for any configuration. For 9 × 9-bit mode, one `addnsub[1..0]` signal controls the top two one-level adders and another `addnsub[1..0]` signal controls the bottom two one-level adders. A high `addnsub` signal indicates addition, and a low signal indicates subtraction. The `addnsub` control signal can be unregistered or registered once or twice when feeding the adder blocks to match data path pipelines.

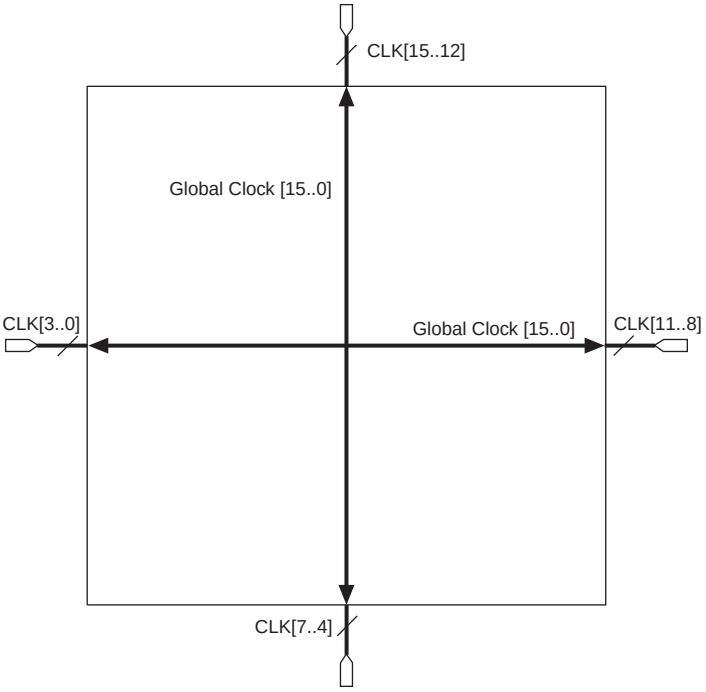
The `signa` and `signb` signals serve the same function as the multiplier block `signa` and `signb` signals. The only difference is that these signals can be registered up to two times. These signals are tied to the same `signa` and `signb` signals from the multiplier and must be connected to the same clocks and control signals.

Accumulator
When configured for accumulation, the adder/output block output feeds back to the accumulator as shown in Figure 2–34. The `accum_sload[1..0]` signal synchronously loads the multiplier result to the accumulator output. This signal can be unregistered or registered once or twice. Additionally, the `overflow` signal indicates the accumulator has overflowed or underflowed in accumulation mode. This signal is always registered and must be externally latched in LEs if the design requires a latched `overflow` signal.

Summation

The output of the adder/subtractor/accumulator block feeds to an optional summation block. This block sums the outputs of the DSP block multipliers. In 9 × 9-bit mode, there are two summation blocks providing the sums of two sets of four 9 × 9-bit multipliers. In 18 × 18-bit mode, there is one summation providing the sum of one set of four 18 × 18-bit multipliers.

Figure 2–42. Global Clocking Note (1)



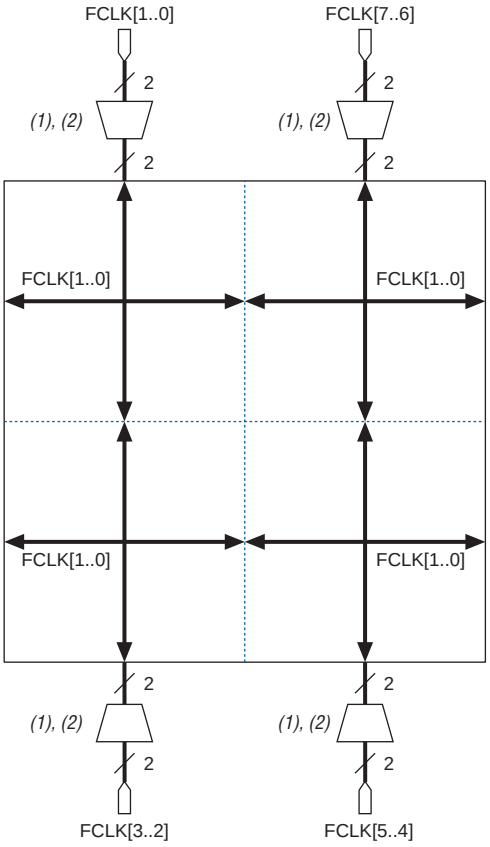
Note to Figure 2–42:

(1) The corner fast PLLs can also be driven through the global or regional clock networks. The global or regional clock input to the fast PLL can be driven by an output from another PLL, a pin-driven global or regional clock, or internally-generated global signals.

Regional Clock Network

There are four regional clock networks within each quadrant of the Stratix device that are driven by the same dedicated CLK[15..0] input pins or from PLL outputs. From a top view of the silicon, RCLK[0..3] are in the top left quadrant, RCLK[8..11] are in the top-right quadrant, RCLK[4..7] are in the bottom-left quadrant, and RCLK[12..15] are in the bottom-right quadrant. The regional clock networks only pertain to the quadrant they drive into. The regional clock networks provide the lowest clock delay and skew for logic contained within a single quadrant. RCLK cannot be driven by internal logic. The CLK clock pins symmetrically drive the RCLK networks within a particular quadrant, as shown in Figure 2–43. See Figures 2–50 and 2–51 for RCLK connections from PLLs and CLK pins.

Figure 2–44. EP1S25, EP1S20 & EP1S10 Device Fast Clock Pin Connections to Fast Regional Clocks



Notes to Figure 2–44:
(1) This is a set of two multiplexers.
(2) In addition to the FCLK pin inputs, there is also an input from the I/O interconnect.

Figure 2–49 shows a top-level diagram of the Stratix device and PLL floorplan.

Figure 2–49. PLL Locations

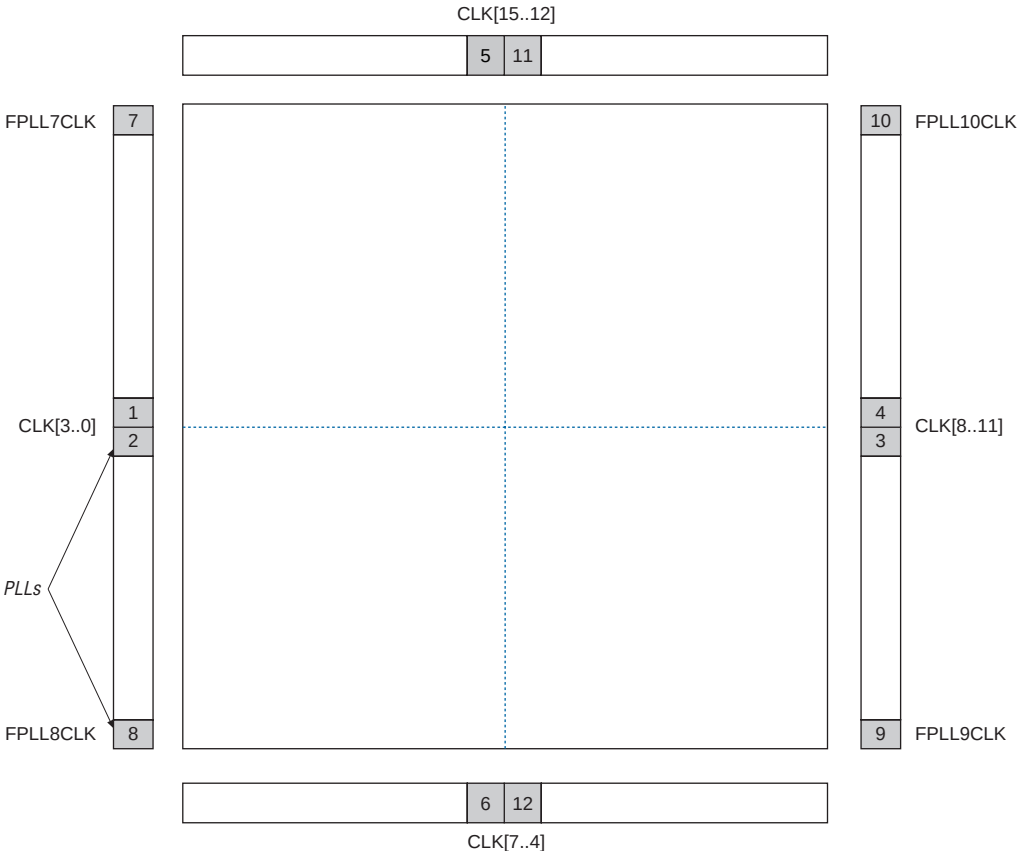
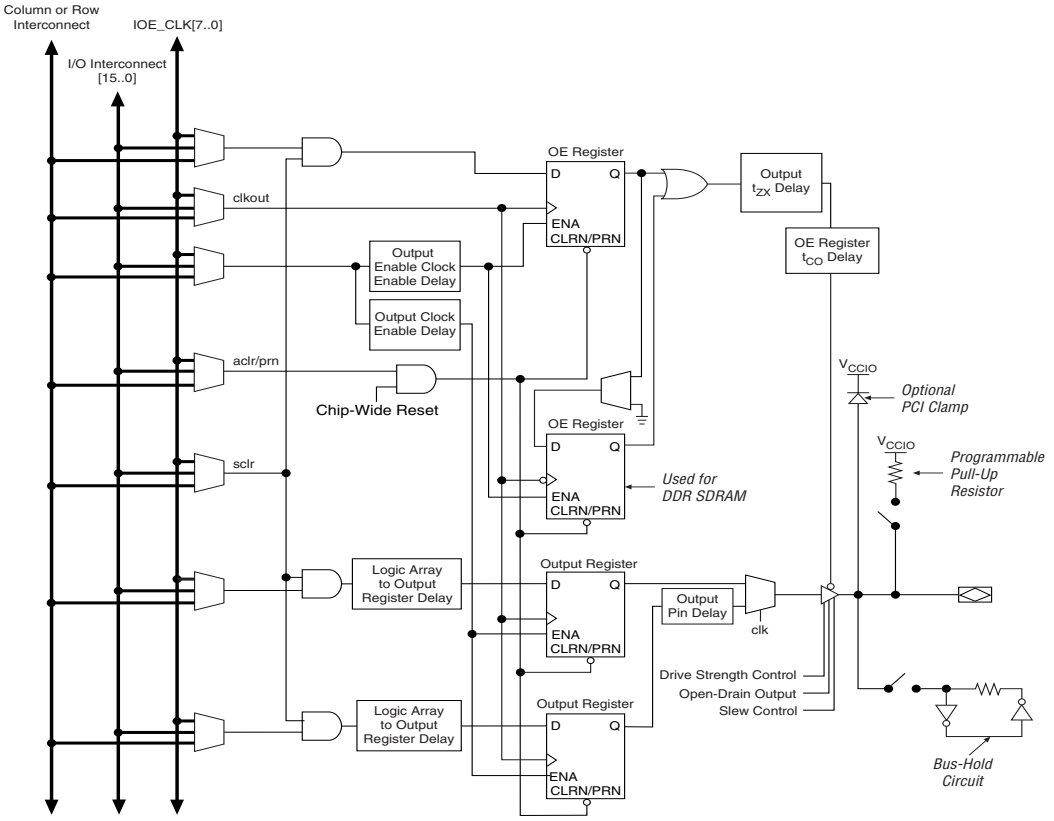


Figure 2–67. Stratix IOE in DDR Output I/O Configuration Notes (1), (2)



Notes to Figure 2–67:

(1) All input signals to the IOE can be inverted at the IOE.

(2) The tristate is by default active high. It can, however, be designed to be active low.

Table 2–32. I/O Support by Bank (Part 2 of 2)

I/O Standard	Top & Bottom Banks (3, 4, 7 & 8)	Left & Right Banks (1, 2, 5 & 6)	Enhanced PLL External Clock Output Banks (9, 10, 11 & 12)
SSTL-3 Class II	✓	✓	✓
AGP (1× and 2×)	✓		✓
CTT	✓	✓	✓

Each I/O bank has its own VCCIO pins. A single device can support 1.5-, 1.8-, 2.5-, and 3.3-V interfaces; each bank can support a different standard independently. Each bank also has dedicated VREF pins to support any one of the voltage-referenced standards (such as SSTL-3) independently.

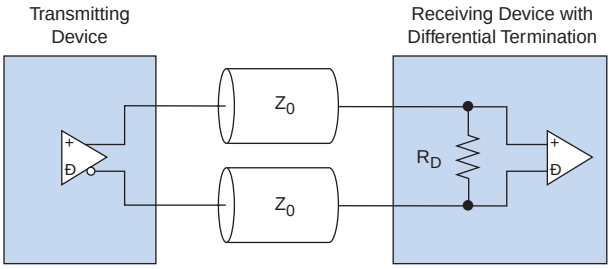
Each I/O bank can support multiple standards with the same V_{CCIO} for input and output pins. Each bank can support one voltage-referenced I/O standard. For example, when V_{CCIO} is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

Differential On-Chip Termination

Stratix devices provide differential on-chip termination (LVDS I/O standard) to reduce reflections and maintain signal integrity. Differential on-chip termination simplifies board design by minimizing the number of external termination resistors required. Termination can be placed inside the package, eliminating small stubs that can still lead to reflections. The internal termination is designed using transistors in the linear region of operation.

Stratix devices support internal differential termination with a nominal resistance value of 137.5 Ω for LVDS input receiver buffers. LVPECL signals require an external termination resistor. Figure 2–71 shows the device with differential termination.

Figure 2–71. LVDS Input Differential On-Chip Termination



I/O banks on the left and right side of the device support LVDS receiver (far-end) differential termination.

Table 2–33 shows the Stratix device differential termination support.

Table 2–33. Differential Termination Supported by I/O Banks

Differential Termination Support	I/O Standard Support	Top & Bottom Banks (3, 4, 7 & 8)	Left & Right Banks (1, 2, 5 & 6)
Differential termination *(1)*, *(2)*	LVDS		✓

Notes to Table 2–33:
(1) Clock pin CLK0, CLK2, CLK9, CLK11, and pins FPLL[7..10]CLK do not support differential termination.
(2) Differential termination is only supported for LVDS because of a 3.3-V V_{CCIO}.

Table 2–34 shows the termination support for different pin types.

Table 2–34. Differential Termination Support Across Pin Types

Pin Type	R_D
Top and bottom I/O banks (3, 4, 7, and 8)	
DIFFIO_RX[]	✓
CLK[0,2,9,11],CLK[4-7],CLK[12-15]	
CLK[1,3,8,10]	✓
FCLK	
FPLL[7..10]CLK	

The differential on-chip resistance at the receiver input buffer is 118 Ω ±20 %.

However, there is additional resistance present between the device ball and the input of the receiver buffer, as shown in Figure 2–72. This resistance is because of package trace resistance (which can be calculated as the resistance from the package ball to the pad) and the parasitic layout metal routing resistance (which is shown between the pad and the intersection of the on-chip termination and input buffer).

Figure 2–72. Differential Resistance of LVDS Differential Pin Pair (R_D)

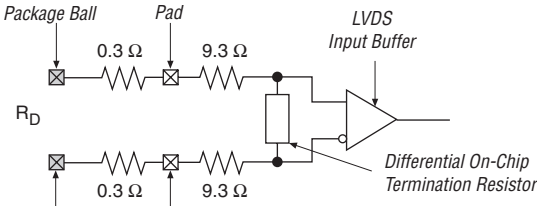


Table 2–35 defines the specification for internal termination resistance for commercial devices.

Table 2–35. Differential On-Chip Termination

Symbol	Description	Conditions	Resistance			Unit
			Min	Typ	Max	
R_D *(2)*	Internal differential termination for LVDS	Commercial *(1)*, *(3)*	110	135	165	W
		Industrial *(2)*, *(3)*	100	135	170	W

Notes to Table 2–35:

(1) Data measured over minimum conditions (T_j = 0 C, V_{CCIO} +5%) and maximum conditions (T_j = 85 C, V_{CCIO} = –5%).

(2) Data measured over minimum conditions (T_j = –40 C, V_{CCIO} +5%) and maximum conditions (T_j = 100 C, V_{CCIO} = –5%).

(3) LVDS data rate is supported for 840 Mbps using internal differential termination.

MultiVolt I/O Interface

The Stratix architecture supports the MultiVolt I/O interface feature, which allows Stratix devices in all packages to interface with systems of different supply voltages.

The Stratix VCCINT pins must always be connected to a 1.5-V power supply. With a 1.5-V V_{CCINT} level, input pins are 1.5-V, 1.8-V, 2.5-V, and 3.3-V tolerant. The VCCIO pins can be connected to either a 1.5-V, 1.8-V, 2.5-V, or 3.3-V power supply, depending on the output requirements.

Table 4–7. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage		1.65	1.95	V
V_{IH}	High-level input voltage		0.65 × V_{CCIO}	2.25	V
V_{IL}	Low-level input voltage		–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OH} = –2 to –8 mA *(10)*	V_{CCIO} – 0.45		V
V_{OL}	Low-level output voltage	I_{OL} = 2 to 8 mA *(10)*		0.45	V

Table 4–8. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage		1.4	1.6	V
V_{IH}	High-level input voltage		0.65 × V_{CCIO}	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OH} = –2 mA *(10)*	0.75 × V_{CCIO}		V
V_{OL}	Low-level output voltage	I_{OL} = 2 mA *(10)*		0.25 × V_{CCIO}	V

Notes to Tables 4–1 through 4–8:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.

(2) Conditions beyond those listed in Table 4–1 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse affects on the device.

(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns, or overshoot to the voltage shown in Table 4–9, based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.

(5) V_{CCIO} maximum and minimum conditions for LVPECL, LVDS, and 3.3-V PCML are shown in parentheses.

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.

(7) Typical values are for T_A = 25°C, V_{CCINT} = 1.5 V, and V_{CCIO} = 1.5 V, 1.8 V, 2.5 V, and 3.3 V.

(8) This value is specified for normal device operation. The value may vary during power-up. This applies for all V_{CCIO} settings (3.3, 2.5, 1.8, and 1.5 V).

(9) Pin pull-up resistance values will lower if an external source drives the pin higher than V_{CCIO}.

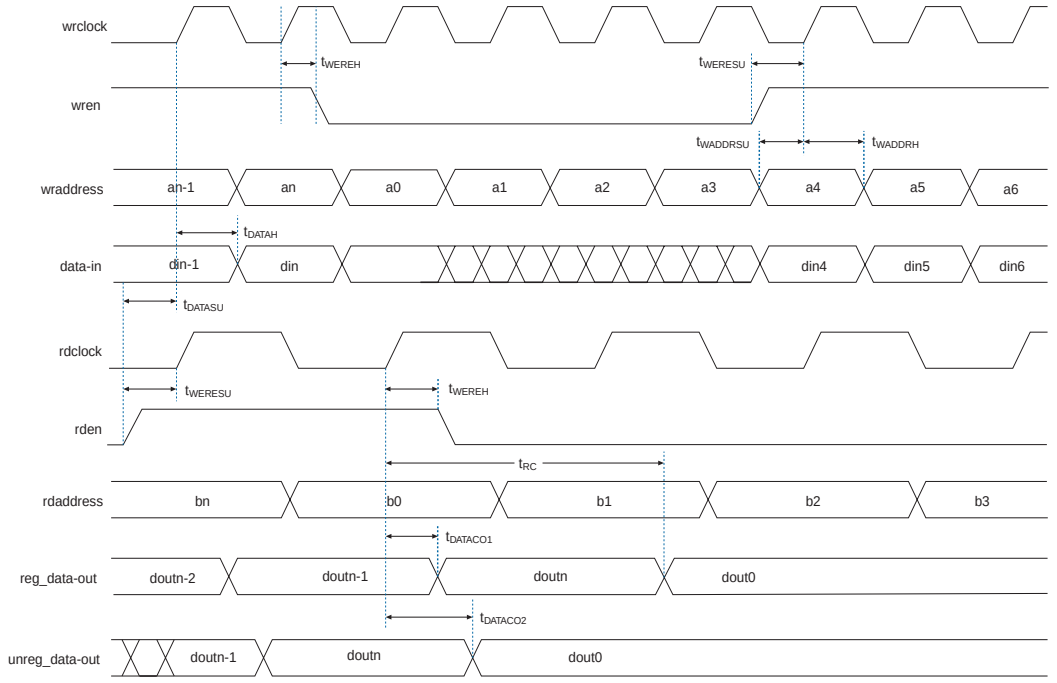
(10) Drive strength is programmable according to the values shown in the *Stratix Architecture* chapter of the *Stratix Device Handbook, Volume 1*.

Table 4–9. Overshoot Input Voltage with Respect to Duty Cycle (Part 1 of 2)

Vin (V)	Maximum Duty Cycle (%)
4.0	100
4.1	90
4.2	50

Figure 4–3 shows the TriMatrix memory waveforms for the M512, M4K, and M-RAM timing parameters shown in Tables 4–40 through 4–42.

Figure 4–3. Dual-Port RAM Timing Microparameter Waveform



Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–44 through 4–50 show the internal timing microparameters for LEs, IOEs, TriMatrix memory structures, DSP blocks, and MultiTrack interconnects.

Table 4–43. Routing Delay Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t_{R4}	Delay for an R4 line with average loading; covers a distance of four LAB columns.
t_{R8}	Delay for an R8 line with average loading; covers a distance of eight LAB columns.
t_{R24}	Delay for an R24 line with average loading; covers a distance of 24 LAB columns.

Stratix External I/O Timing

These timing parameters are for both column IOE and row IOE pins. In EP1S30 devices and above, you can decrease the t_{SU} time by using the FPLLCLK, but may get positive hold time in EP1S60 and EP1S80 devices. You should use the Quartus II software to verify the external devices for any pin.

Tables 4–55 through 4–60 show the external timing parameters on column and row pins for EP1S10 devices.

Table 4–55. EP1S10 External I/O Timing on Column Pins Using Fast Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.238		2.325		2.668		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.240	4.549	2.240	4.836	2.240	5.218	NA	NA	ns
t_{XZ}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns
t_{ZX}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns

Table 4–56. EP1S10 External I/O Timing on Column Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max			
t_{INSU}	1.992		2.054		2.359		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.395	4.795	2.395	5.107	2.395	5.527	NA	NA	ns
t_{XZ}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
t_{ZX}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
$t_{INSUPLL}$	0.975		0.985		1.097		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA	NA	ns
$t_{OUTCOPLL}$	1.262	2.636	1.262	2.680	1.262	2.769	NA	NA	ns
t_{XZPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns
t_{ZXPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns

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